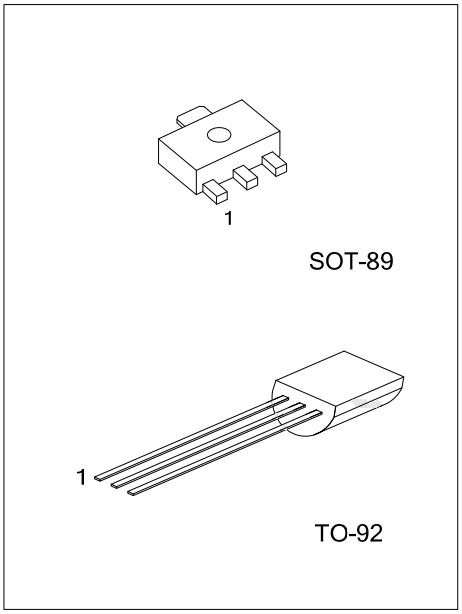
2N3904

NPN SILICON TRANSISTOR

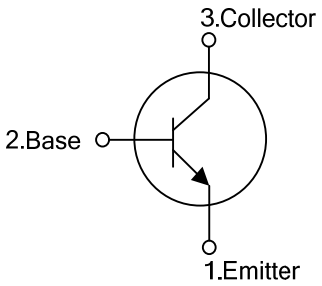
NPN GENERAL PURPOSE AMPLIFIER



■ FEATURES

* Collector-Emitter Voltage: V_{CEO}=40V
* Complementary to 2N3906

■ FEATURES



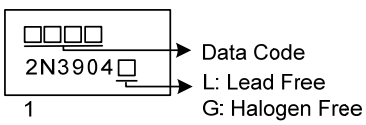
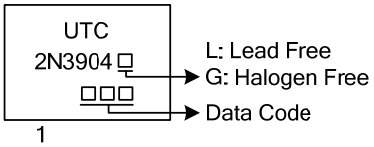
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N3904L-AB3-R	2N3904G-AB3-R	SOT-89	B	C	E	Tape Reel
2N3904L-T92-B	2N3904G-T92-B	TO-92	E	B	C	Tape Box
2N3904L-T92-K	2N3904G-T92-K	TO-92	E	B	C	Bulk

Note: Pin Assignment: B: Base C: Collector E: Emitter

2N3904G-AB3-R (1)Packing Type (2)Package Type (3)Green Package	(1) B: Tape Box, K: Bulk, R: Tape Reel (2) AB3: SOT-89, T92: TO-92 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING

SOT-89	TO-92
	

■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	60	V
Collector-Emitter Voltage		V_{CEO}	40	V
Emitter-Base Voltage		V_{EBO}	6	V
Collector Current		I_C	200	mA
Collector Dissipation	SOT-89	P_C	500	mW
	TO-92		625	
Junction Temperature		T_J	+150	°C
Operating and Storage Temperature		T_{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	SOT-89	θ_{JA}	220	°C/W
	TO-92		200	°C/W
Junction to Case	SOT-89	θ_{JC}	38	°C/W
	TO-92		83.3	°C/W

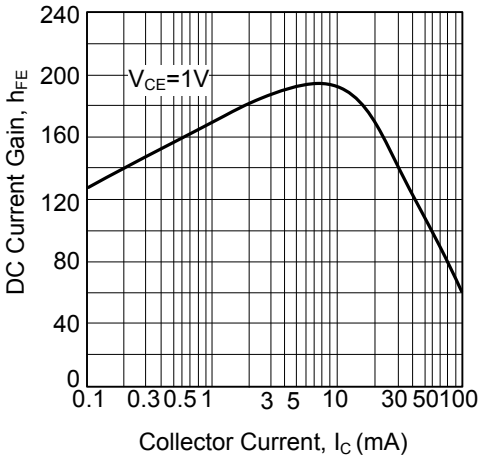
■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=10μA, I_E=0	60			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=1mA,I_B=0 (Note)	40			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=10μA, I_C=0	6			V
Collector-Emitter Saturation Voltage (Note)	$V_{CE(SAT)1}$	I_C=10mA, I_B=1mA			0.2	V
	$V_{CE(SAT)2}$	I_C=50mA, I_B=5mA			0.3	V
Base-Emitter Saturation Voltage (Note)	$V_{BE(SAT)1}$	I_C=10mA, I_B=1mA	0.65		0.85	V
	$V_{BE(SAT)2}$	I_C=50mA, I_B=5mA			0.95	V
Collector Cut-off Current	I_{CBO}	V_{CE}=30V, V_{EB}=3V			50	nA
Base Cut-off Current	I_{BL}	V_{CE}=30V, V_{EB}=3V			50	nA
DC Current Gain (note)	h_{FE1}	V_{CE}=1V, I_C=0.1mA	40			
	h_{FE2}	V_{CE}=1V, I_C=1mA	70			
	h_{FE3}	V_{CE}=1V, I_C=10mA	100		300	
	h_{FE4}	V_{CE}=1V, I_C=50mA	60			
	h_{FE5}	V_{CE}=1V, I_C=100mA	30			
Current Gain Bandwidth Product	f_T	V_{CE}=20V, I_C=10mA, f=100MHz	300			MHz
Output Capacitance	C_{OB}	V_{CB}=5V, I_E=0, f=1MHz			4	pF
Turn on Time	t_{ON}	V_{CC}=3V,V_{BE}=0.5V,I_C=10mA, I_B1=1mA			70	ns
Turn off Time	t_{OFF}	I_B1=1_B2=1mA			250	ns

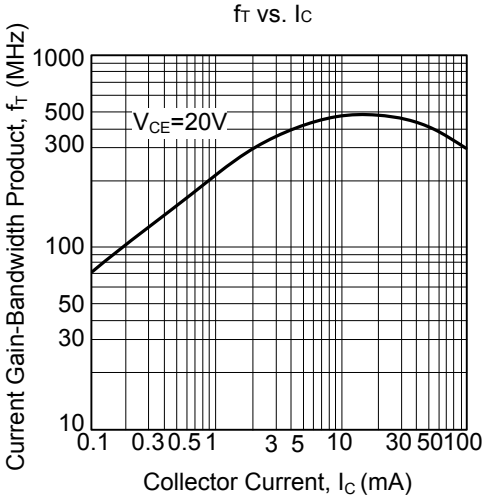
Note: Pulse test: Pulse Width≦300μs, Duty Cycle≦2%

■ TYPICAL CHARACTERISTICS

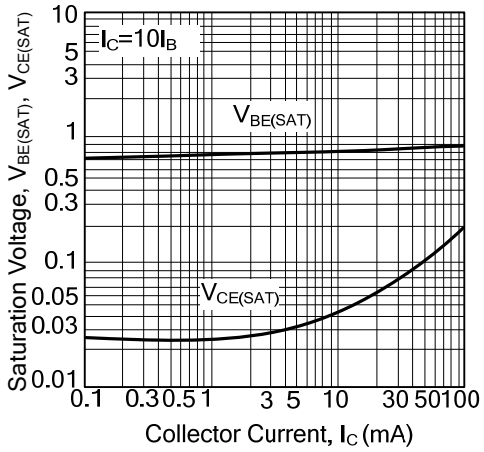
h_{FE} vs. I_C



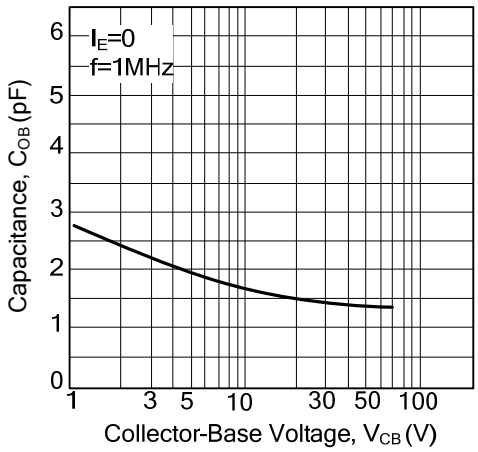
f_T vs. I_C



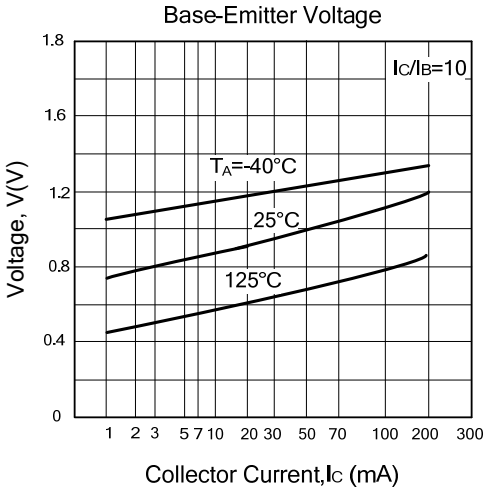
$V_{(SAT)}$ vs. I_C



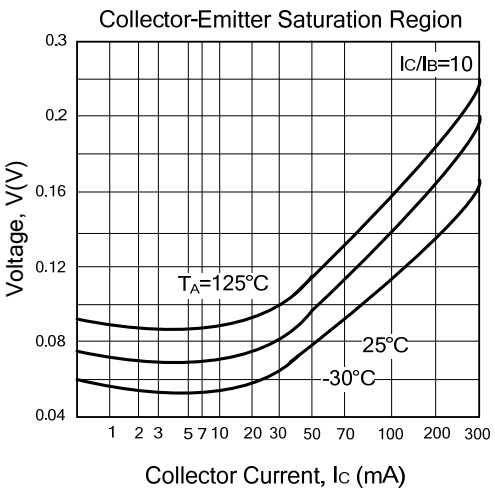
C_{OB} vs. V_{CB}



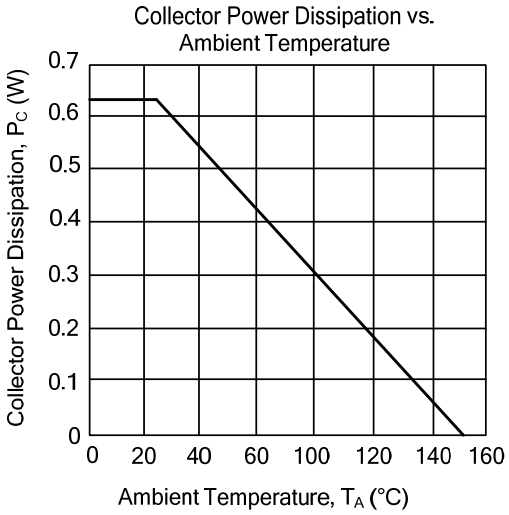
Base-Emitter Voltage



Collector-Emitter Saturation Region



■ TYPICAL CHARACTERISTICS(Cont.)



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